DISCRETE SEMICONDUCTORS

DATA SHEET

PMBF4391; PMBF4392; PMBF4393

N-channel FETs

Product specification

April 1995



N-channel FETs

PMBF4391; PMBF4392; PMBF4393

DESCRIPTION

Symmetrical silicon n-channel depletion type junction field-effect transistors on a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power chopper or switching applications in industry.

PINNING

1 = drain

2 = source

3 = gate

Note

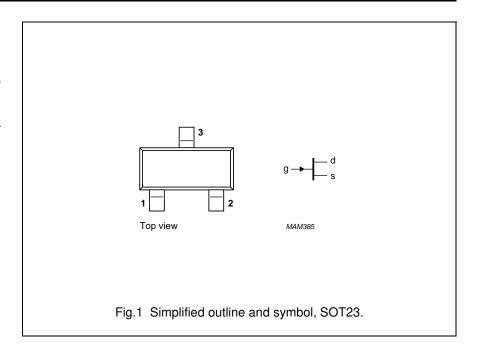
1. Drain and source are interchangeable.

Marking code

PMBF4391 = p6J

PMBF4392 = p6K

PMBF4393 = p6G



QUICK REFERENCE DATA

		PMBF4391		PMBF4392	392 PMBF439		
Drain-source voltage	$\pm \ V_{DS}$	max.	40	40	40	V	_
Drain current							
$V_{DS} = 20 \text{ V}; V_{GS} = 0$	I_{DSS}	>	50	25	5	mA	
Gate-source cut-off voltage							
$V_{DS} = 20 \text{ V; } I_D = 1 \text{ nA}$	$-V_{(P)GS}$	>	4	2	0.5	V	
VDS = 20 V, ID = 1 IIA	- v (P)GS	<	10	5	3	V	
Drain-source resistance (on) at f = 1 kHz							
$I_D = 0; V_{GS} = 0$	$R_{ds\ on}$	<	30	60	100	Ω	
Feedback capacitance at f = 1 MHz							
$-V_{GS} = 12 \text{ V}; V_{DS} = 0$	C_{rs}	<	3.5	3.5	3.5	pF	
Turn-off time							
$V_{DD} = 10 \text{ V}; V_{GS} = 0$							
$I_D = 12 \text{ mA}; -V_{GSM} = 12 \text{ V}$	t_{off}	<	20	_	_	ns	
$I_D = 6 \text{ mA}; -V_{GSM} = 7 \text{ V}$	t_{off}	<	_	35	_	ns	
$I_D = 3 \text{ mA}; -V_{GSM} = 5 \text{ V}$	t_{off}	<	_	_	50	ns	

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RATINGS								
	accordance with the Absolute Max	kimum Svstem (IEC 13	34)				
Drain-source volta		, (√ _{DS}	max.	40	V	
Drain-gate voltage			V _{DGO}		max.	40		
Gate-source voltage				' _{GSO}	max.	40	V	
Gate current (DC)	-		I_{G}		max.		mΑ	
, ,	ation up to $T_{amb} = 40 ^{\circ}C^{(1)}$		Pto		max.	250	mW	
Storage temperatu			Ts		-65 to + 150		°C	
Junction temperat	_		Tj	-9	max.	150	°C	
THERMAL RESIST	TANCE							
From junction to a	mbient ⁽¹⁾		Rt	h j-a	=	430	K/W	
CHARACTERISTIC								
$T_j = 25 ^{\circ}\text{C} \text{ unless o}$								
Gate-source voltage	•							
$I_G = 1 \text{ mA}; V_{DS} = 1 \text{ mA}$				V_{GSon}	<		1	V
Gate-source cut-o								
$V_{DS} = 0 V; -V_{GS}$				-I _{GSS}	<		0.1	nA •
$V_{DS} = 0 \text{ V}; -V_{GS} = 20 \text{ V}; T_{amb} = 150 ^{\circ}\text{C}$				-l _{GSS}	< 		0.2	μ A
			PINE	BF4391	PMBF43			4393
Drain current	0	I _{DSS}	>	50	РМВГ43	25	5	mA
Drain current V _{DS} = 20 V; V _{GS}	_S = 0	I _{DSS}	-		РМВГ43			
	-	I _{DSS}	>	50	PMBF43	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$	kdown voltage	I _{DSS} -V _(BR) GSS	>	50	РМВГ43	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source break	kdown voltage = 0		> <	50 150	РМВГ43	25 75	5 30	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_{G}$ = 1 μ A; V_{DS}	kdown voltage = 0 ff voltage	−V _(BR) GSS	> <	50 150	РМВГ43	25 75 40	5 30 40	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} =	kdown voltage = 0 ff voltage = 20 V age (on)	−V _(BR) GSS −V _(P) GS	> < < > >	50 150 40 4 10	РМВГ43	25 75 40 2	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-o I_D = 1 nA; V_{DS} = Drain-source volta I_D = 12 mA; V_{GS}	<pre>cdown voltage = 0 ff voltage = 20 V age (on) s = 0</pre>	$-V_{(BR)GSS}$ $-V_{(P)GS}$ V_{DSon}	> < < > >	50 150 40 4	РМВГ43	25 75 40 2 5	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-oo I_D = 1 nA; V_{DS} = Drain-source volta I_D = 12 mA; V_{GS} I_D = 6 mA; V_{GS}	kdown voltage = 0 ff voltage = 20 V age (on) $6 = 0$ = 0	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> <	50 150 40 4 10	РМВГ43	25 75 40 2	5 30 40 0.5	mA mA V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 0$ $Drain\text{-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 0$ $I_D = 6 \text{ mA; } V_{GS} = 0$ $I_D = 3 \text{ mA; } V_{GS} = 0$	<pre>cdown voltage = 0 ff voltage = 20 V age (on) s = 0 = 0 = 0</pre>	$-V_{(BR)GSS}$ $-V_{(P)GS}$ V_{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10	РМВГ43	25 75 40 2 5	5 30 40 0.5 3	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-oo I_D = 1 nA; V_{DS} = Drain-source voltat I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} = I_D = 3 mA; V_{GS} = Drain-source resis	kdown voltage = 0 ff voltage = 20 V age (on) $6 = 0$ = 0 = 0 stance (on)	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> < > < < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4	РМВГ43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-or $I_D = 1 \text{ nA; } V_{DS} = 0$ Drain-source voltat $I_D = 12 \text{ mA; } V_{GS} = 0$ $I_D = 6 \text{ mA; } V_{GS} = 0$ Drain-source resist $I_D = 0; V_{GS} = 0;$	kdown voltage = 0 ff voltage = 20 V age (on) $6 = 0$ = 0 = 0 etance (on) $6 = 1 \text{ kHz}; T_{amb} = 25 ^{\circ}\text{C}$	$\begin{array}{c} -V_{(BR)GSS} \\ -V_{(P)GS} \end{array}$ $\begin{array}{c} V_{DSon} \\ V_{DSon} \end{array}$	> < > < < < < < < < < < < < < < < < < <	50 150 40 4 10	РМВГ43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A; } V_{DS}$ Gate-source cut-or $I_D = 1 \text{ nA; } V_{DS} = 1 \text{ Drain-source volta}$ $I_D = 12 \text{ mA; } V_{GS} = 1 \text{ Drain-source resis}$ $I_D = 3 \text{ mA; } V_{GS} = 1 \text{ Drain-source resis}$ $I_D = 0; V_{GS} = 0;$ Drain cut-off curre	kdown voltage = 0 ff voltage = 20 V age (on) $S = 0$ = 0 = 0 stance (on) $f = 1 \text{ kHz}; T_{amb} = 25 ^{\circ}\text{C}$ nt	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4 -	РМВГ43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source break $-I_G = 1 \mu\text{A}; V_{DS}$ Gate-source cut-o $I_D = 1 \text{ nA}; V_{DS} = 1 \text{ mA}; V_{DS} = 1 \text{ mA}; V_{GS} = 1 $	kdown voltage = 0 ff voltage = 20 V age (on) $6 = 0$ = 0 = 0 etance (on) $6 = 1 \text{ kHz}; T_{amb} = 25 ^{\circ}\text{C}$	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} r _{ds on}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4	РМВГ43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 0$ $I_D = 12 \text{ mA; } V_{GS} = 0$ $I_D = 6 \text{ mA; } V_{GS} = 0$ $I_D = 3 \text{ mA; } V_{GS} = 0$ $Drain\text{-source resis}$ $I_D = 0; V_{GS} = 0;$ $Drain\text{-cut-off curre}$ $-V_{GS} = 12 \text{ V}$ $-V_{GS} = 7 \text{ V}$	kdown voltage = 0 ff voltage = 20 V age (on) $S = 0$ = 0 = 0 stance (on) $f = 1 \text{ kHz}; T_{amb} = 25 ^{\circ}\text{C}$ nt	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX}	> <	50 150 40 4 10 0.4 -	РМВГ43	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 100 \text{ M}$ $I_D = 12 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 6 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 3 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 0; V_{GS} = 0;$ $I_D = 0; V_{GS} = 0;$ $I_D = 0; V_{GS} = 100 \text{ M}$	kdown voltage = 0 ff voltage = 20 V age (on) S = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt V _{DS} = 20 V	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -	РМВГ43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V O nA nA
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 1000 \text{ may } V_{GS} = 10000 \text{ may } V_{GS} = 1000 \text{ may } V_{GS} = 10000 \text{ may } V_{GS} = 1000 \text{ may } V_{GS} = 10000 \text{ may } V_{GS}$	kdown voltage = 0 ff voltage = 20 V age (on) $S = 0$ = 0 = 0 stance (on) $f = 1 \text{ kHz}; T_{amb} = 25 ^{\circ}\text{C}$ nt	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} I _{DSX} I _{DSX} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -	РМВГ43	25 75 40 2 5 - 0.4 - - - 0.1	5 30 40 0.5 3	mA mA V V V V V V V A nA nA nA μA
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-o}$ $I_D = 1 \text{ nA; } V_{DS} = 100 \text{ M}$ $I_D = 12 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 6 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 3 \text{ mA; } V_{GS} = 100 \text{ M}$ $I_D = 0; V_{GS} = 0;$ $I_D = 0; V_{GS} = 0;$ $I_D = 0; V_{GS} = 100 \text{ M}$	kdown voltage = 0 ff voltage = 20 V age (on) S = 0 = 0 = 0 stance (on) f = 1 kHz; T _{amb} = 25 °C nt V _{DS} = 20 V	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -	РМВГ43	25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V O nA nA

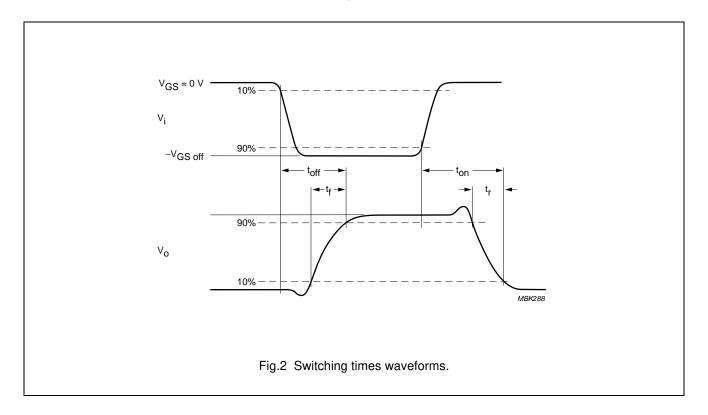
N-channel FETs

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y-parameters (common source)						
V_{DS} = 20 V; V_{GS} = 0; f = 1 MHz; T_{amb} = 25 °C		PMB	F4391	PMBF4392	PMBF	4393
Input capacitance	C_{is}	<	14	14	14	pF
Feedback capacitance						
$-V_{GS} = 12 \text{ V}$; $V_{DS} = 0$	C_{rs}	<	3.5	_	_	pF
$-V_{GS} = 7 V$; $V_{DS} = 0$	C_{rs}	<	_	3.5	_	pF
$-V_{GS} = 5 V$; $V_{DS} = 0$	C_{rs}	<	_	_	3.5	pF
Switching times						
$V_{DD} = 10 \text{ V}$; $V_{DS} = 0$						
Conditions I _D and -V _{GSoff}	I_D	=	12	6	3	mA
	$-V_{GS\ off}$	=	12	7	5	V
	R_L	=	750	1550	3150	Ω
Rise time	t_r	<	5	5	5	ns
Turn on time	t _{on}	<	15	15	15	ns
Fall time	t _f	<	15	20	30	ns
Turn off time	t_{off}	<	20	35	50	ns

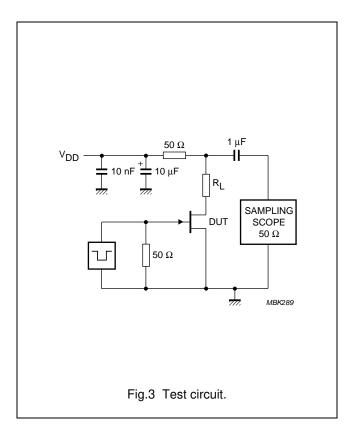
Note

1. Mounted on a ceramic substrate of 8 mm \times 10 mm \times 0,7 mm.



N-channel FETs

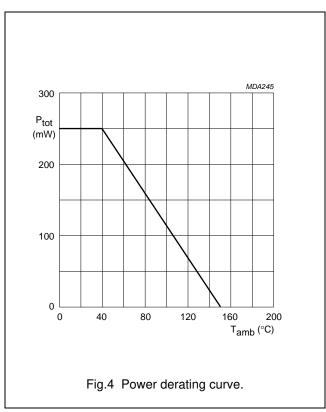
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Pulse generator:

 $\begin{array}{llll} t_r & < & 0.5 & \text{ns} \\ t_f & < & 0.5 & \text{ns} \\ t_p & = & 100 & \mu \text{s} \\ \delta & = & 0.01 & \\ \\ \text{Oscilloscope:} \end{array}$

 $R_i = 50 \Omega$



N-channel FETs

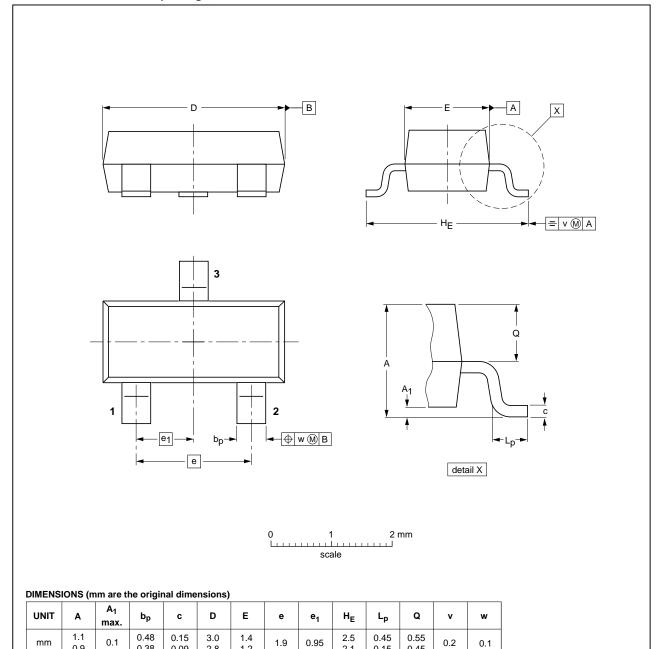
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT23		TO-236AB				-04-11-04 06-03-16

2.1

April 1995 6

0.38

0.9

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DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com

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